

Silicon Darlington power transistors

BD676A/678A/680A

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T-33-31

DESCRIPTION

PNP epitaxial base transistors in a monolithic Darlington circuit in a TO-126 (SOT32) plastic envelope intended for audio and video applications. NPN complements are BD675A, BD677A and BD679A respectively.

PINNING - TO-126 (SOT32)

PIN	DESCRIPTION
1	emitter
2	collector
3	base

Collector connected to mounting base.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	—	45	V	
	BD676A					
	BD678A					
	BD680A					
$-V_{CEO}$	collector-emitter voltage	open base	—	45	V	
	BD676A					
	BD678A					
	BD680A					
$-I_C$	collector current	average value	—	—	4	A
P_{tot}	total power dissipation	$T_{nb} = 25^\circ\text{C}$	—	—	40	W
T_J	junction temperature		—	—	150	$^\circ\text{C}$
h_{FE}	DC current gain	$-I_C = 2 \text{ A}; -V_{CE} = 3 \text{ V}$	750	—	—	
f_{fle}	cut-off frequency	$-I_C = 1.5 \text{ A}; -V_{CE} = 3 \text{ V}$	—	60	—	kHz

PIN CONFIGURATION

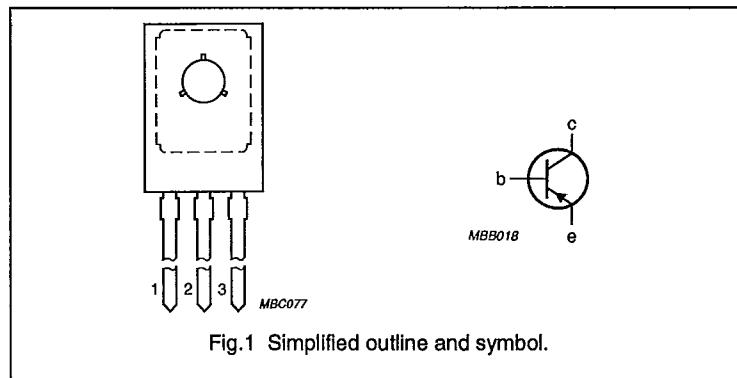


Fig.1 Simplified outline and symbol.

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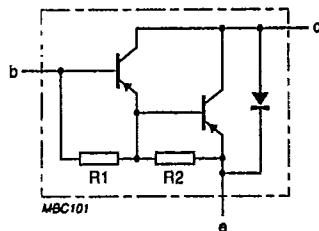
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R1 typ. 3 kΩ

R2 typ. 80 Ω

Fig.2 Darlington circuit diagram.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$-V_{CBO}$	collector-base voltage	open emitter	-	45	V
	BD676A			60	V
	BD678A			80	V
$-V_{CEO}$	collector-emitter voltage	open base	-	45	V
	BD676A			60	V
	BD678A			80	V
$-V_{EBO}$	emitter-base voltage	open collector	-	5	V
$-I_C$	collector current	average value	-	4	A
$-I_{CM}$	collector current	peak value	-	6	A
$-I_B$	base current		-	100	mA
P_{tot}	total power dissipation	$T_{mb} = 25^\circ\text{C}$	-	40	W
T_{stg}	storage temperature range		-65	+150	$^\circ\text{C}$
T_J	junction temperature		-	+150	$^\circ\text{C}$

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THERMAL CHARACTERISTICS

CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	NOM.	UNIT
$R_{th \ j-mb}$	from junction to mounting base		3.12	K/W
$R_{th \ j-a}$	from junction to ambient	in free air	100	K/W
<hr/>				
$-I_{CBO}$	collector cut off current	$I_E = 0;$ $-V_{CB} = -V_{CBO \ max}$	-	0.2 mA
		$I_E = 0;$ $-V_{CB} = -0.5 V_{CBO \ max}$ $T_{mb} = 150^\circ\text{C}$	-	1 mA
$-I_{EBO}$	emitter cut off current	$I_C = 0;$ $-V_{EB} = 5 \text{ V}$	-	5 mA
h_{FE}	DC current gain	$-I_C = 2 \text{ A};$ $-V_{CE} = 3 \text{ V}$	750	-
$-V_{BE}$	base-emitter voltage	$-I_C = 2 \text{ A};$ $-V_{CE} = 3 \text{ V};$ note 1 note 2	-	2.5 V
$-V_{CE \ sat}$	collector-emitter saturation voltage	$-I_C = 2 \text{ A};$ $-I_B = 40 \text{ mA}$ note 1	-	2.8 V
h_{re}	small signal current gain	$-I_C = 1.5 \text{ A};$ $-V_{CE} = 3 \text{ V};$ $f = 1 \text{ MHz}$	10	-

Notes

1. Measured under pulse conditions; $t_p < 300 \mu\text{s}$, $\delta < 2\%$.
2. V_{BE} decreases by typ. 2.3 mV/K with increasing temperature.

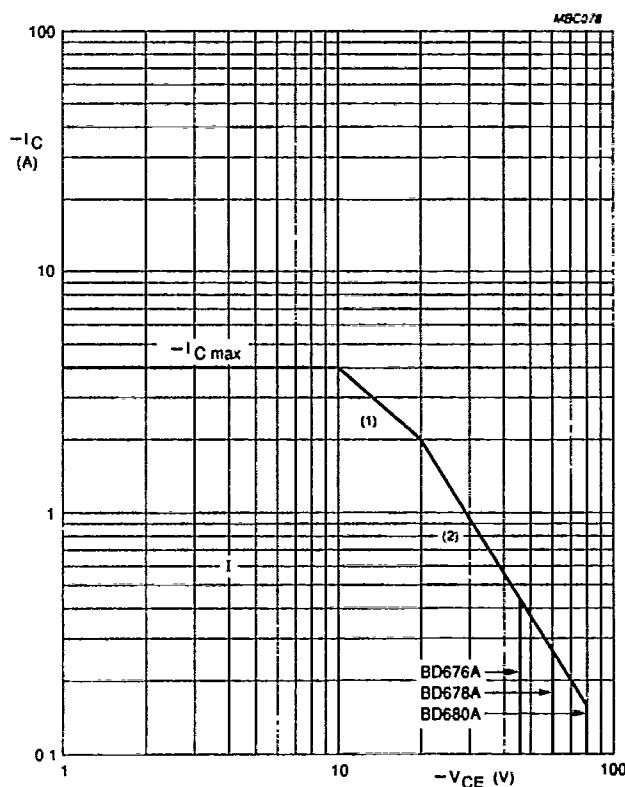
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$$T_{mb} = 25 \text{ }^{\circ}\text{C}$$

I Region of permissible DC operation.

(1) $P_{tot\ max}$ line.

(2) Second breakdown limits.

Fig.3 Safe operating area.

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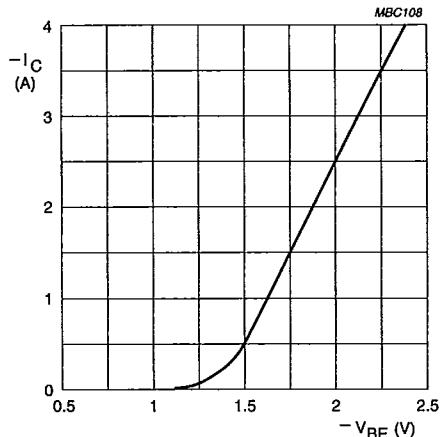
 $-V_{CE} = 3$ V, $T_j = 25$ °C.

Fig.4 Base-emitter voltage as a function of collector current.

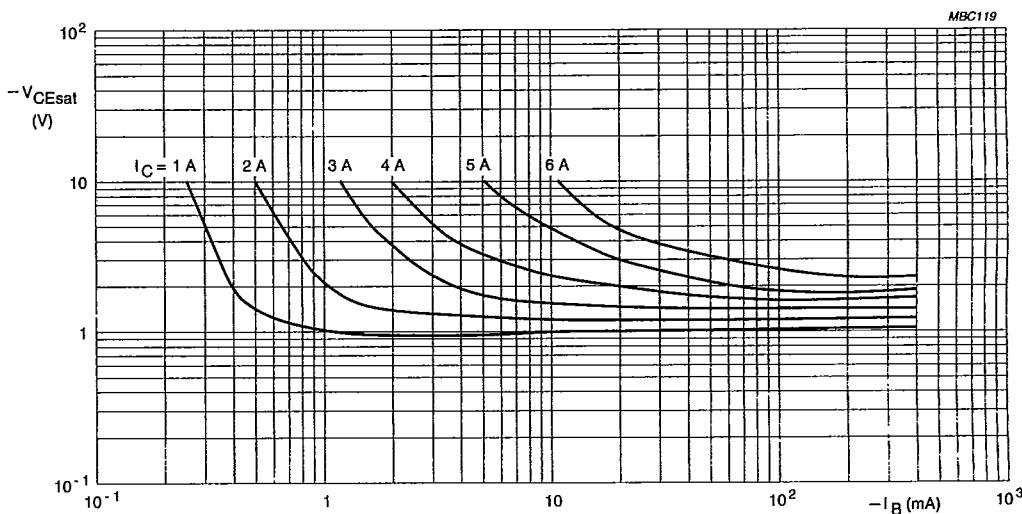
 $T_{mb} = 25$ °C.

Fig.5 Typical values collector-emitter saturation voltage.

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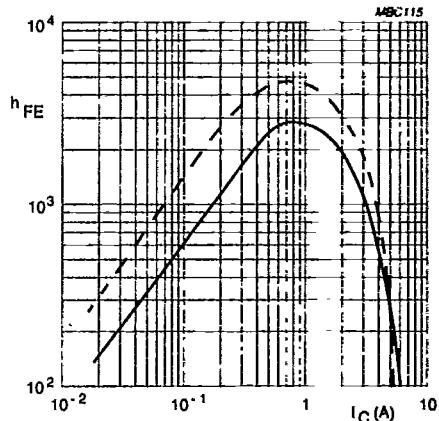
 $-V_{CE} = 3$ V.Solid line = $T_j \approx 25$ °C.Dotted line = $T_j = 125$ °C.

Fig.6 DC current gain.

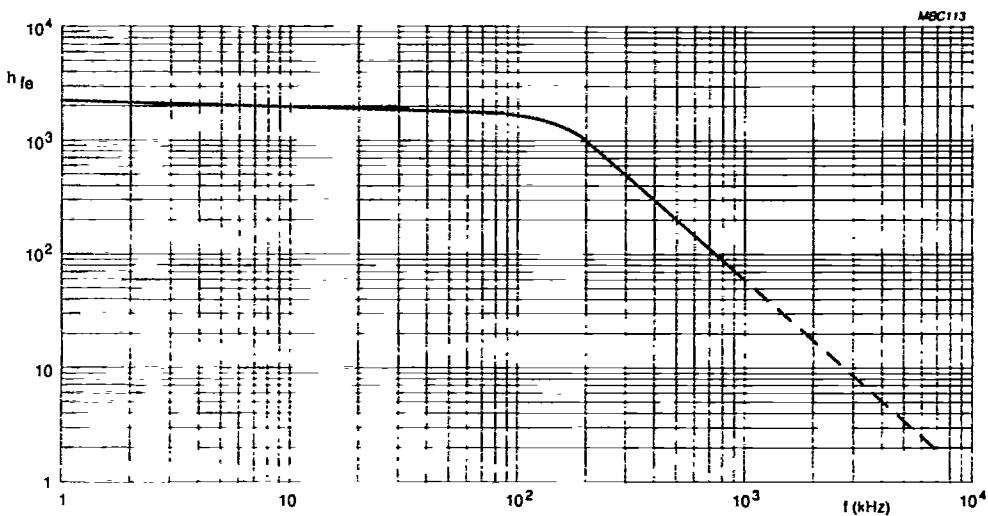
 $-I_C = 1.5$ A, $-V_{CE} = 3$ V.

Fig.7 Typical values small signal current gain.

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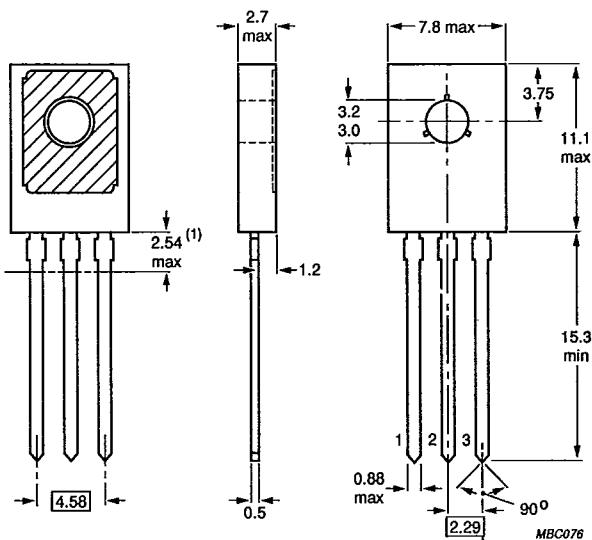
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PACKAGE OUTLINE

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Dimensions in mm

Collector connected to mounting base.

(1) Within this region the cross-section of the leads is uncontrolled

Fig.8 TO-126 (SOT32).